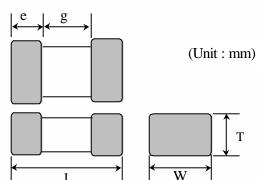
Specification Sheet

< Chip Monolithic Ceramic Capacitor>

Murata Global P/N: GRM31MF51E105ZA01L (1206,Y5V,1uF,25V)



L	W	Т	e	g
3.2+/-0.15	1.6+/-0.15	1.15+/-0.1	0.3 to 0.8	1.5 min.



Rated Value

TC code	TC	DC Rated	CAI		CAP.TOL
		Voltage (V)			
F5	Y5V	25	1	uF	+80/-20%

Packaging

G : C: .:	D 1 ' '
Specification	Packaging unit
	[pcs/reel]
φ178 Plastic Tape Carrier Packaging	3000

Specification

Please refer to next page.

<Notice>

- (1) This specification sheet is applied for CHIP MONOLITHIC CERAMIC CAPACITOR used for General Electronics equipment for your design.
- (2) Please contact our sales representative or product engineers before using our products for the application listed below.
 - (1) Aircraft equipment (2) Aerospace equipment (3) Undersea equipment (4) Medical equipment
 - (5) Transportation equipment (6) Traffic signal equipment (7) Disaster prevention / crime prevention equipment
 - (8) Application of similar complexity and/or requirements to the applications listed in the above.
- (3) Please do not use this specification sheet for quality contract.

If you need to exchange quality contract, please request us to provide the full product specification (including part number construction, available capacitance range, packaging and caution notes) for approval.

Product Engineering Department Monolithic Ceramic Capacitor Group FUKUI MURATA MFG. CO., LTD.

l .								ODS	T						
. I1	tem	Tempera Compensati		Specifi	ication High D	ielectric	: Туре					Test	Method	d	
Operating T Range	emperature	-55°C to +125°C	<u> </u>	R R C E	4:10°C to +8	-125°C -105°C 35°C									
Rated Volta	age	See the previous pa	iges.						applied superi	d cont	tinuously to sed on DC v	the capa	acitor. W	/hen AC volta	
	Э														
												oryod wh	on 200%	of the rated	voltage (AC to
Strength	2								7U and applied charge	d 1X) d betv e/ disc	or 250% of ween the te charge curr	the rate rmination ent is les	d voltage ns for 1 to s than 50	e (R6, R7,C8, o 5 seconds, 0mA.	E4 and F5) is provided the
		(whichever is smalle	er)						exceed minute	ding t	he rated vo	oltage at 2	25°C and	d 75%RH ma	x. and within
Capacitanc	е	Within the specified	toleran	ce.											at the
Q/		30pFmin.:Q≥1000	Char	25\/ min	16\/	101/	6 21/	41.7		y a					
Dissipation (D.F.)	Factor	30pFmax.: Q≥400+20C C:Nominal Capacitance (pF)	R6 R7 C8	0.025 max	x. 0.035 max.		0.05n (C<3. 0.1m	max. .3μF) nax.	Char		ΔC to 7U, 1X 1000pF and below)	to 70 (more that R6,R7	J, 1X n 1000pF) ',C8,F5	R6,R7,F5 (C>10μF)	E4
			F5				0.15		Freque	ency	1±0.1MHz	1±0.	.1kHz	120± 24Hz	1±0.1kHz
				0.09 max	. 0.09 max.	max.	max.	_	Voltage	e (0.5 to 5Vrms	1±0.2	2Vrms	0.5±0.1Vrms	0.5±0.05Vrms
	Change Temperature Coefficent	tolerance. (Table A-1) Within the specified (Table A-1) Within ±0.2% or ±0.(Whichever is large	R6 R7 C8 E4 F5 tolerand	-55°C ~ -55°C ~ -55°C ~ +10°C ~	+85°C +125°C 25°C +105°C -+85°C	w W W	ithin ±15 ithin ±15 ithin ±22 +22 ithin -56	5% 5% 2%	(2) Hi The ravalue withir Initial	pecifipperacimpe	ied temperature Comporature Comporature coefficients of the composition of the coefficients of the coeffic	interestage ensating ficient is a sa referse of through to +85°C efor the as Table a	ge. Type determine ence. Wh h 5 (ΔC:- :) the cap temperat A-1. The ferences sis in the s	d using the canen cycling the +25°C to +12 pacitance shature coefficier capacitance between the step 1,3 and 5 ture(°C) -2 R6/R7/C8) r E4) -2 pared with the win the tab constant type C for one ho	apacitance le temperature 5°C, other Il be within and drift is e maximum b by the cap 8) e above 25°C le shall be
		A Line te		Fig.1	Solde	er resist	ode or		Fig.1 u the tes The so methor	ising st jig f olderir d and	a eutectic s for 10±1sec ng shall be d shall be co	solder. The second seco	nen apply ner with a l with carr ch as hea 5N (GR □ 2N (GR □ a 0.3 0.4 .0 .2 2.2	n iron or usin e sothat the s tt shock 115, GRM18)	n parallel with
	Appearance Dimension Dielectric Strength Insulation F Capacitance Q/ Dissipation (D.F.) Capacitance Temperature Character- istics	Appearance Dimension Dielectric Strength Insulation Resistance Capacitance Q/ Dissipation Factor (D.F.) Capacitance Temperature Character- istics Capacitance Change Temperature Coefficent Capacitance	Appearance Dimension Dimension Dielectric Strength Insulation Resistance Q/ Dissipation Factor (D.F.) Capacitance Character-istics Capacitance Capacitance Character-istics Rated Voltage No defects or abnor Within the specified No defects or abnor Within the specified Within the specified 30pFmax.: Q≥1000 30pFmax.: Q≥400+20C C:Nominal Capacitance (pF) Capacitance Change Change Within the specified tolerance. (Table A-1) Capacitance Drift Within the specified Within the specified Within the specified Within the specified No apply to 1 N/2	Rated Voltage See the previous pages. Appearance Dimension Dielectric Strength Insulation Resistance Within the specified dimens No defects or abnormalities Within the specified tolerance (whichever is smaller) Capacitance Within the specified tolerance (Capacitance (PF) Capacitance (Character-istics) Capacitance Change Character-istics Capacitance Character-istics Capacitanc	Rated Voltage See the previous pages. Appearance Dimension Dielectric Strength Insulation Resistance More than 10,000MΩ or 500Ω-F. (whichever is smaller) Capacitance Within the specified tolerance. Q/ Dissipation Factor (D.F.) Capacitance Capacitance Capacitance Character- Istics Capacitance Within the specified tolerance. Within the specified tolerance. C:Nominal Capacitance (pF) Capacitance Character- Istics Within the specified tolerance. (Capacitance Change Character- Istics Within the specified tolerance. (Table A-1) Within the specified tolerance. (Table A-1) Capacitance Capacitance Capacitance Capacitance Character- Istics No removal of the terminations or other termination.	Rated Voltage See the previous pages. Appearance Dimension Dimension Dielectric Strength Insulation Resistance More than 10,000MΩ or 500Ω-F. (whichever is smaller) Capacitance Within the specified dimensions. Objectic Strength Insulation Resistance Within the specified tolerance. O/ Dissipation Factor (D.F.) Capacitance C:Nominal Capacitance (pF) Capacitance Character- istics Capacitance Within the specified Tolerance, Capacitance Character- istics Capacitance Character- istics Within the specified tolerance, Capacitance Character- istics Within the specified Tolerance, Character- istics Capacitance Character- istics No removal of the terminations or other defect shall of the termination No removal of the terminations or other defect shall of the termination No removal of the terminations or other defect shall of the termination No removal of the terminations or other defect shall of the termination or	Cas : 45°C to +105°C E4 : 10°C to +485°C E4	Rated Voltage See the previous pages.	California Capacitance Capacitance	Rated Voltage See the previous pages. Rated Voltage See the previous pages. See the previous pages. Appearance No defects or abnormalities. Dimension Within the specified dimensions. Using loss pages. Insulation Resistance Within the specified tolerance. Capacitance Within the specified tolerance. Within the specified tolerance. Capacitance Cinominal Capacitance (pF) Capacitance (Capacitance (pF) Capacitance Ca	Rated Voltage See the previous pages. See the previous pages. See the previous pages. Appearance No defects or abnormalities. No defects or abnormal	Capacitance No defects or abnormalities. No defects or abnormal	Rated Voltage See the previous pages. Appearance No deficts or abnormalities. No deficts or abnormalities. No deficts or abnormalities. No deficts or abnormalities. No failure shall be observed with Using capital within the specified differences. No failure shall be observed with Using capital within the rated voltage is defined as applied continuously to the cape to maintained within the rated. Within the specified differences. No failure shall be observed with Using capital previous and previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. No failure shall be observed with Using capital previous pages. 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Capacitance Capacitance Capacitance Capacitance Within the specified information. Capacitance Cap

		SPE	CIFICATION	IS /	AND TE	ST ME	THC	DDS				P 2	
					Specifica	ation							
No.	lte	em	Temperatu Compensating)	High Die	lectric ⁻	Туре		Test Method			
11	Vibration	Appearance	No defects or abnorm	alities	i.						capacitor to the test jig (g		
	Resistance	Capacitance Q/D.F.	Within the specified to	olerano	ce.			er and under the same on all be subjected to a sim	, ,				
		Q/D.F.	30pFmin.:Q <u>≥</u> 1000 30pFmax.:	Chai	25V min.	16V	10V	6.3V		1 '	al amplitude of 1.5mm, t	•	
			Q <u>≥</u> 400+20C	R6 R7	0.025 max.	0.035 max	0.035 max		5 max. 3.3μF)		etween the approximate I ange, from 10 to 55Hz ar		
			C:Nominal	C8				0.1	max. 3.3μF)		ange, nom 10 to 55112 at approximately 1 minute.		
			Capacitance (pF)	E4	0.025 max.	-	_	(02	_ _		a period of 2 hours in each	ch 3 mutually perpend	dicula
				F5	0.05 max. (C<0.1μF)	0.07 max. (C<1.0μF)	0.128 max			directions(to	otal of 6 hours).		
					0.09 max. (C≥0.1μF)	0.09 max. (C≥1.0μF)		. IIIax.					
12	Deflection		No cracking or marki	na def	ects shall occi	lir				Solder the o	capacitor on the test jig (rlass enoxy hoard) sh	hown
-	Bonoonon		The ordering of marking	ig doi	0000 011011 0000	ui.					ng a eutectic solder. Ther		
											own in Fig 3 for 5±1sec. with an iron or using the	_	
											with care so that the sold		
										defects such	h as heat shock.		
				2	0₁/ 50						ф4.5	Ŧ	
				Y	Pressu speed:	ınzıng :1.0mm/sed	.					₽	
			_R23	ى_لا	ア Pressu						<u> </u>	1	
			7		7	#				k	100		
				~~~	Fسکا إ	lexure: <u>≤</u> 1					Fig.2	t: 1.6mm	
			!	•	itance mete					Tv	ype a b	(GR□03,GR□15:0.8mn	n)
			<del> </del>	45	45					GR	□03 0.3 0.9	0.3	
				Fi	g.3						□15 0.4 1.5 M18 1.0 3.0		
										GR	M21 1.2 4.0	1.65 (in a	mm)
											M31 2.2 5.0 M32 2.2 5.0	2.0	,
											M43 3.5 7.0		
										GR	M55 4.5 8.0	5.6	
13	Solderability	<b>of</b>	75% of the terminatio	ns is t	o be soldered	evenly and	continuo	usly.			e capacitor in a solution	*	,
	Termination									,	(-5902) (25% rosin in wei (25% for 10 to 30 seconds. A	0 1 1 /	
											solder solution for 2±0.5		
14	Resistance to Soldering Hea								tions in	Preheat the capacitor at *120 to 150°C for 1 minute. Immerse the capacitor in a eutectic solder solution at 270±5°C for			
		Appearance	No marking defects.						onds. Let sit at room tem e compensating ty pe) or				
		Capacitance	Within ±2.5% or ±0.25	5pF		,C8:Within ±7	.5%			constant typ	be), then measure.		
		Change Q/D.F.	(Whichever is larger) 30pFmin.:Q≥1000			Within ±20%				· Initial mea	surement for high dielect	ric constant type	
		Q/D.F.	20n Emay .	Char. R6	25V min. 0.025 max. 0	16V	10V 0.035	6.3V 0.05 r	4V	Perform a h	eat treatment at 150 + 0 °	C for one hour and the	hen le
			Q <u>≥</u> 400+20C	R7	0.025 IIIAX. C	7.033 IIIAX.	max.	(C<3.3	3μF)		hours at room temperatue initial measurement.	ire.	
			C:Nominal	C8				0.1m (C <u>≥</u> 3.3	ax. 3μF)				
			Capacitance (pF)	E4	0.025 max.	-	-	-		*Preheating	g for GRM32/43/55	<u> </u>	
			l [	F5		0.07 max. (C<1.0μF)	0.125 max.	0.15 max.	- ]	Step	Temperature	Time	
					0.09 max.	0.09 max. (C <u>≥</u> 1.0μF)				1	100°C to 120°C	1 min.	
	Ī					_				2	170°C to 200°C	1 min.	
		I P	More than 40 000140	or For	O E/\\/\:\-		-1						
		I.R. Dielectric	More than 10,000M $\Omega$	or 500	Ω · F(Whiche	ever is smalle	r)						

		5	SPECIFICATI	ON	S ANI	) TEST	MET	HOI	DS				P 3			
					Specif	ication					<u> </u>					
No.	lte	em	Tempera Compensatir		e e	High Di	electric	: Туре		<u> </u>	Tes	t Metho	d			
15	Temperature	Cycle	The measured and ol the following table.			istics shall satis	fy the s	pecifica	ations in	under the sar	me conditions a	s (10). Pe	n the same mar rform the five cy	cles		
		Appearance	No marking defects.							_			isted in the follo ure compensatir	•		
		Capacitance	Within ±2.5% or ±0.25	5pF	,	R7,C8:Within ±7	.5%				s (high dielectric			ig type)		
		Change	(Whichever is larger)					<del>.                                     </del>	then measure							
		Q/D.F.	30pFmin.:Q <u>≥</u> 1000 30pFmax.:	Char R6	25V min. 0.025 ma	16V x. 0.035 max.	10V 0.035	6.3V 0.05	5 max.	Step Temp.(°C)	1 Min.	2 Room	3 Max.	4 Room		
			Q <u>≥</u> 400+20C	R7 C8			max.	(C<	3.3μF) max. 3.3μF)	Time	Operating Temp. +0/-3	Temp.	Operating Temp. +3/-0	Temp.		
			C:Nominal	E4	0.025 ma	x. –	-	(02	- -	Time (min.)	30±3	2 to 3	30±3	2 to 3		
			Capacitance (pF)	F5	0.05 max (C<0.1µF 0.09 max (C≥0.1µF	0.07 max. (C<1.0μF) 0.09 max.	0.125 max.	0.15 max.	-	Perform a hea	urement for high at treatment at o	150 +0°C	for one hour ar	nd then let		
		I.R.	More than 10,000M $\Omega$	or 500			\ \			Perform the in	nitial measurem	ent				
		Dielectric	No failure	01 000	22 1 (********	nover le dinaner	<i>,</i>			1						
		Strength	The familie													
16	Humidity		The measured and of	serve	d characte	istics shall satis	fy the s	pecifica	ations in			and 90 to	95% humiduty	for		
	Steady State	Appearance	the following table.  No marking defects.							500±12 hours Remove and	Remove and let sit for 24±2 hours (temperature compensating					
			Within ±5% or ±0.5pF R6,R7,C8:Within ±12.5%							type) or 48±4	type) or 48±4 hours (high dielectric constant type) at room temperature, then measure.					
		Change	(Whichever is larger)	. II <del>ai</del>		4,F5:Within ±30		2.21		temperature,	then measure.					
		Q/D.F.	30pF and over:Q≥350 10pF and over, 30pF and below: Q≥275+ $\frac{5}{2}$ C 10pF and below: Q≥200+10C C:Nominal Capacitance(pF)	Ch R R C	6 0.05 n	nin. 16V nax. 0.05 max.	0.05 max.	(C<3 0.12	4V 5max. .3μF) 5max. .3μF)							
				F		nax. 0.1 max. μF) (C<1.0μF) nax. 0.125	0.15 max.	0.2 max.	_							
		I.R.	More than 1,000M $\Omega$ o	r 50Ω·	F(Whichev	er is smaller)										
		Dielectric Strength	No failure													
17	Humidity Load	t	The measured and ol the following table.	serve	d characte	istics shall satis	fy the s	pecifica	ations in	Apply the rate 500±12 hours	_	±2°C and	d 90 to 95% hur	nidity for		
		Appearance	No marking defects.							Remove and	let sit for 24±2 l		perature compe	_		
		Capacitance Change	Within ±7.5% or ±0.79 (Whichever is larger)	5pF	E	6,R7,C8:Within 4:Within ±30% 5:Within ±30% 5:Within +30/-4	(W.V.>1	0V)	<b>'</b> )	temprature, the charge/d	nen muasure. ischarge curren	nstant type) at ronan 50mA.	oom			
			30pF and over:Q≥200				10V	6.3V	4V	Apply the rate	rement for F5/1 ed DC voltage for	or 1 hour				
		Q/D.F.	Q/D.F. 30pF and below: Q≥100 + 10/3 C C:Nominal	R6 R7 C8	7		0.05 max.	0.075 (C<3. 0.125 (C≥3.	.3μF) max.	Remove and	nove and let sit for 48±4 hours at room temperature. form initial measurement.			e.		
			Capacitance(pF)	F	0.075 n	nax. 0.1 max. uF) (C<1.0µF) nax. 0.125	0.15 max.	0.2 max.	-							
		I.R.	More than 500M $\Omega$ or :	25Ω·F	(Whicheve	is smaller)				1						
		Dielectric Strength	No failure													

		S	SPECIFICATIO	NS	AND	TEST	MET	HOI	DS		P 4	
No.	No. Item				Specificat	ion	Test Method					
			Temperature High Dielectric Type Compensating Type									
18	Load the following table.  Appearance No marking defects.  Capacitance Within ±3% or ±0.3pF (Whichever is larger)  30pF and over:Q≥350 10pF and over, 30pF and below: Q/D.F. Q≥275+ 5/2 C 10pF and below:			served characteristics shall satisfy the specifications in						maximun operating tempera	ature ±3°C . Let sit for 24±2	
			Within ±3% or ±0.3pF		E4:V F5:V	27,C8:Within /ithin ±30% /ithin±30% (0 /ithin +30/-40	Cap<1.0	0 <u>≥</u> μF)	=)	hours(temperature compensating type) or 48±4 hours(high dielectric constant type) at room temperature, then measure. The charge/discharge current is less than 50mA.  Initial measurement for high dielectric constant type. Apply 200% of the rated DC voltage for one hour at the		
			10pF and over, 30pF and below: Q≥275+ 5/2 C  10pF and below: Q≥200+10C C:Nominal	F5	0.05 max 0.05 max 0.075 max	. 0.1 max. (C<1.0µF) . 0.125	max. 	6.3V 0.075 (C<3 0.125 (C≥3 0.2 max.	.3µF)	maximun operating tempera	ature ±3°C . Remove and let sit for rature.Perform initial measurement.	
			 50Ω·F(V	Vhichever i	(C≥1.0μF) s smaller)							

Table A-1

			(	Capacitance Change from 25 °C (%)									
Char.	Nominal Values	-5	5	-3	30	-10							
	(ppm/∘c ) Note 1	Max.	Min.	Max.	Min.	Max.	Min.						
5C	0± 30	0. 58	-0.24	0.40	-0.17	0.25	-0.11						
6C	0± 60	0.87	-0.48	0.59	-0.33	0.38	-0.21						
6P	-150± 60	2.33	0.72	1.61	0.50	1.02	0.32						
6R	-220± 60	3.02	1.28	2.08	0.88	1.32	0.56						
6S	-330± 60	4.09	2.16	2.81	1.49	1.79	0.95						
6T	-470± 60	5.46	3.28	3.75	2.26	2.39	1.44						
7U	-750±120	8.78	5.04	6.04	3.47	3.84	2.21						
1X	+350~-1000	_	_		—	_							

Note 1:Nominal values denote the temperature coefficient within a range of 25 °C to 125°C (for ΔC)/85°C (for other TC).